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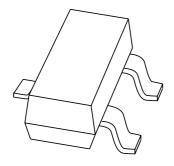
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAW156 Low-leakage double diode

Product data sheet Supersedes data of 1996 Mar 13 1999 May 11



Low-leakage double diode

BAW156

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

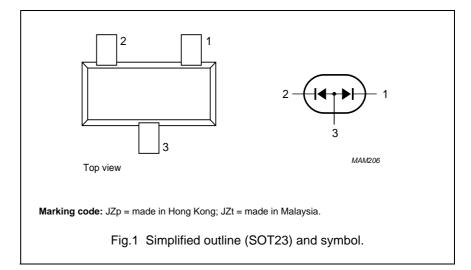
 Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are in common anode configuration.

PINNING

PIN	DESCRIPTION	
1	cathode	
2	cathode	
3	common anode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode	•		1	•	1
V _{RRM}	repetitive peak reverse voltage		_	85	V
V_R	continuous reverse voltage		_	75	V
I _F	continuous forward current	single diode loaded; note 1; see Fig.2	_	160	mA
		double diode loaded; note 1; see Fig.2	_	140	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		$t_p = 1 \mu s$	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		$t_p = 1 s$	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C

Note

1. Device mounted on a FR4 printed-circuit board.

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Low-leakage double diode

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ELECTRICAL CHARACTERISTICS

 T_i = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT	
Per diode						
V _F	forward voltage	see Fig.3				
		I _F = 1 mA	_	900	mV	
		I _F = 10 mA	_	1000	mV	
		I _F = 50 mA	_	1100	mV	
		I _F = 150 mA	_	1250	mV	
I _R	reverse current	see Fig.5				
		V _R = 75 V	0.003	5	nA	
		V _R = 75 V; T _j = 150 °C	3	80	nA	
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	3	_	pF	
t _{rr}	reverse recovery time	when switched from I _F = 10 mA to	0.8	3	μs	
		I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7				

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

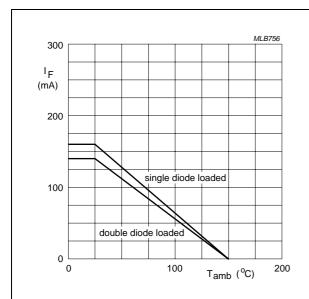
1. Device mounted on a FR4 printed-circuit board.

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Low-leakage double diode

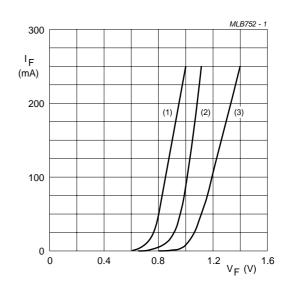
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GRAPHICAL DATA



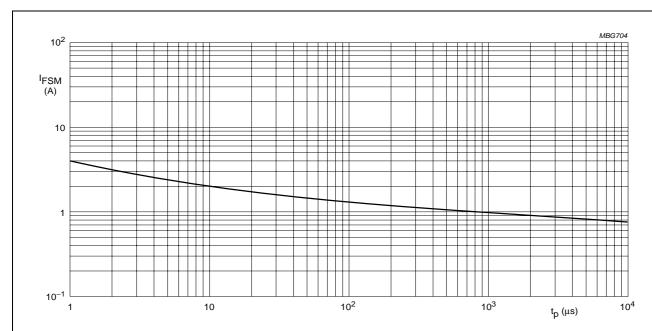
Device mounted on a FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) T_i = 150 °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.



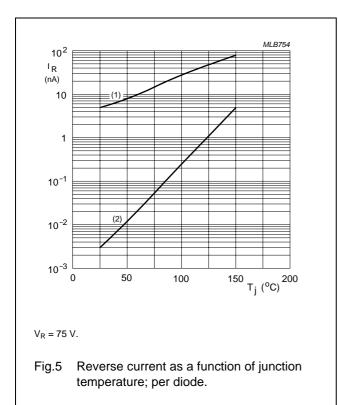
Based on square wave currents. $T_i = 25 \,^{\circ}\text{C}$ prior to surge

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

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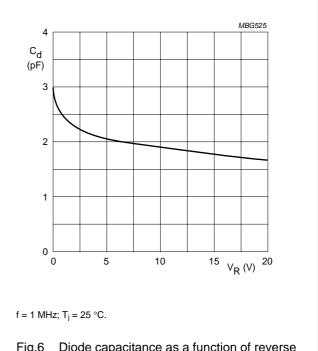
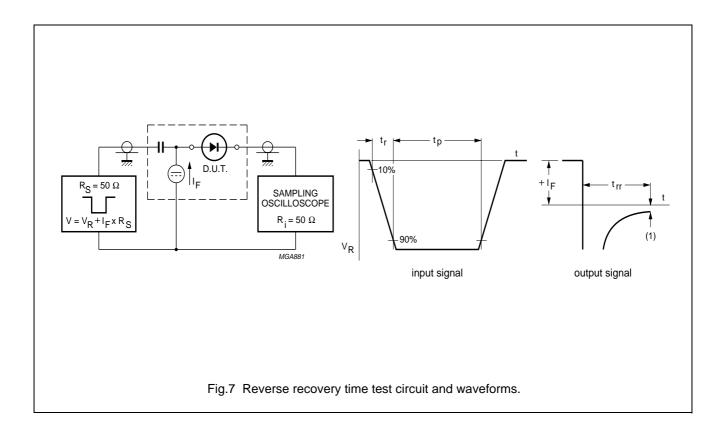


Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.



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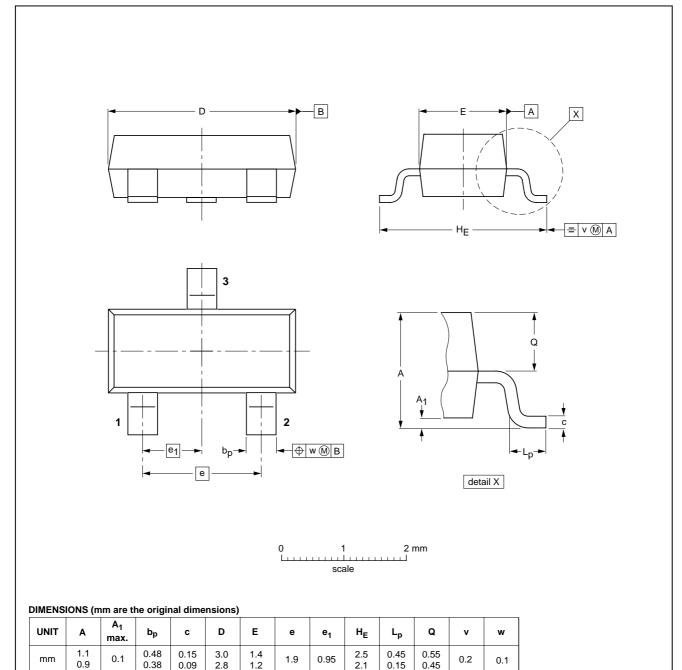
Low-leakage double diode

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION 1550E DA	
SOT23		TO-236AB				-97-02-28- 99-09-13

0.1

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0.38

0.09

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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